

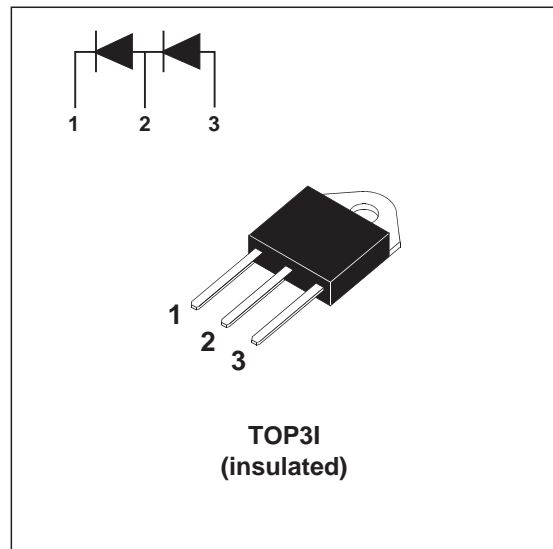
Tandem 600V Hyperfast Rectifier

MAJOR PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	15 A
V_{RRM}	600 V (in series)
T_j (max)	150 °C
V_F (max)	2.6 V
I_{RM} (typ.)	4.8 A

FEATURES AND BENEFITS

- Especially suited as boost diode in continuous mode power factor correctors and hard switching conditions.
- Designed for high di/dt operation. Hyperfast recovery current to compete with GaAs devices. Allows downsizing of mosfet and heatsinks.
- Internal ceramic insulated devices with equal thermal conditions for both 300V diodes.
- Insulation (2500V RMS) allows placement on same heatsink as mosfet and flexible heatsinking on common or separate heatsink.
- Matched diodes for typical PFC application without need for voltage balance network.
- $C = 7\text{pF}$



DESCRIPTION

The TURBOSWITCH "H" is an ultra high performance diode composed of two 300V dice in series. TURBOSWITCH "H" family drastically cuts losses in the associated MOSFET when run at high di/dt.

ABSOLUTE RATINGS (limiting values for both diodes in series)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		600	V
$I_{F(RMS)}$	RMS forward current		26	A
I_{FSM}	Surge non repetitive forward current	tp = 10 ms sinusoidal	130	A
T_{stg}	Storage temperature range		-65 +150	°C
T_j	Maximum operating junction temperature		+ 150	°C

THERMAL AND POWER DATA

Symbol	Parameter	Test conditions	Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	2.9	°C/W
$R_{th(c)}$		Coupling	0.3	
$R_{th(j-c)}$	Junction to case	Total	1.6	
P_1	Conduction power dissipation for both diodes	$I_{F(AV)} = 15\text{ A}$ $\delta = 0.5$ $T_c = 70^\circ\text{C}$	50	W

STATIC ELECTRICAL CHARACTERISTICS (for both diodes)

Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$V_R = V_{RRM}$	$T_j = 25^\circ\text{C}$		20	μA
			$T_j = 125^\circ\text{C}$		30	
V_F^{**}	Forward voltage drop	$I_F = 15\text{ A}$	$T_j = 25^\circ\text{C}$		3.6	V
			$T_j = 125^\circ\text{C}$		2.1	

Pulse test: * $t_p = 5\text{ms}$, $\delta < 2\%$

** $t_p = 380\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation:

$$P = 1.8 \times I_{F(AV)} + 0.053 \times I_F^2_{(RMS)}$$

RECOVERY CHARACTERISTICS

Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit	
t_{rr}	Reverse recovery time	$I_F = 0.5\text{ A}$ $I_{rr} = 0.25\text{ A}$ $I_R = 1\text{ A}$	$T_j = 25^\circ\text{C}$		16	ns	
		$I_F = 1\text{ A}$ $di_F/dt = -50\text{ A}/\mu\text{s}$ $V_R = 30\text{ V}$			35		
I_{RM}	Reverse recovery current	$V_R = 400\text{ V}$ $I_F = 15\text{ A}$ $di_F/dt = -200\text{ A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		4.8	6.0	A
S_{factor}					0.4		-

TURN-ON SWITCHING CHARACTERISTICS

Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit
t_{fr}	Forward recovery time	$I_F = 15\text{ A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$, $V_{FR} = 1.1 \times V_{Fmax}$			200	ns
V_{FP}	Forward recovery voltage	$I_F = 15\text{ A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$			6	V

Fig. 1: Conduction losses versus average current.

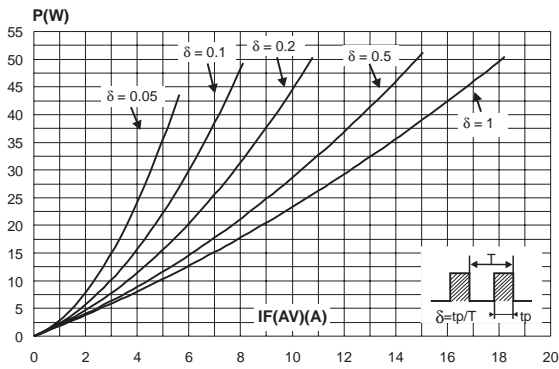


Fig. 2: Forward voltage drop versus forward current.

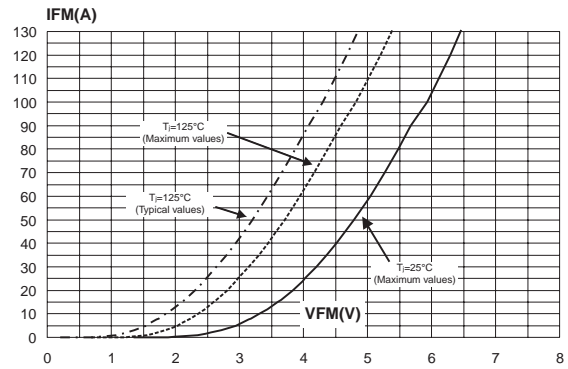


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

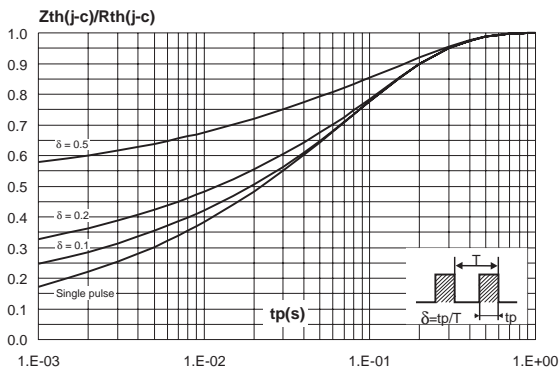


Fig. 4: Peak reverse recovery current versus di_F/dt (90% confidence).

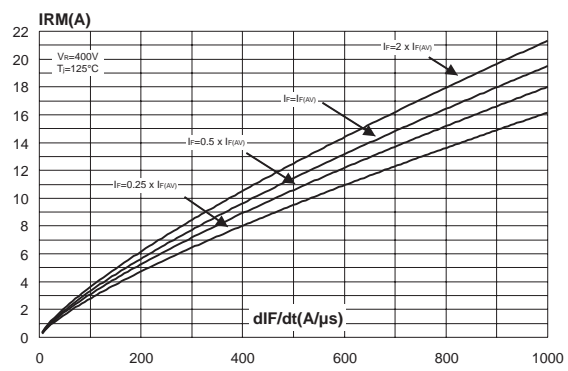


Fig. 5: Reverse recovery time versus di_F/dt (90% confidence).

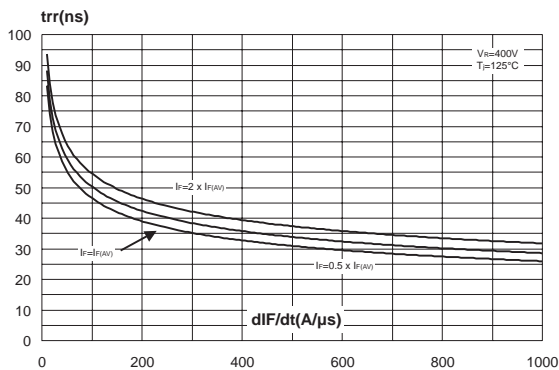


Fig. 6: Reverse recovery charges versus di_F/dt (90% confidence).

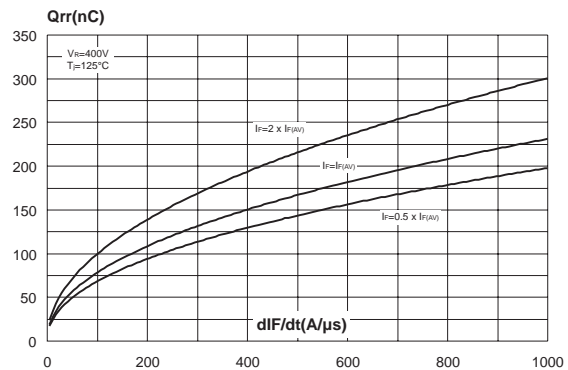


Fig. 7: Softness factor versus dI_F/dt (typical values).

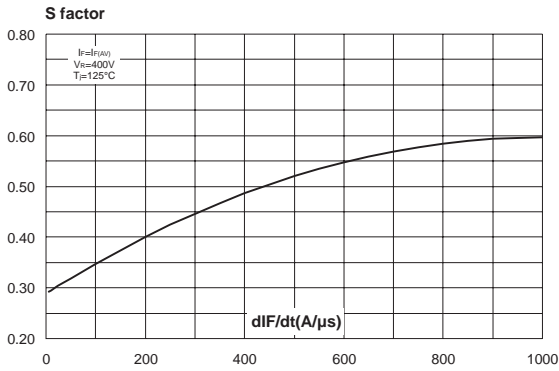


Fig. 8: Relative variations of dynamic parameters versus junction temperature.

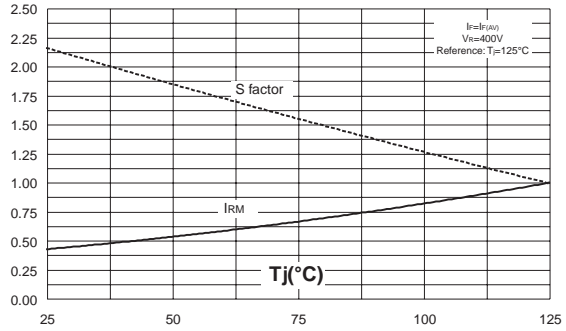


Fig. 9: Transient peak forward voltage versus dI_F/dt (90% confidence).

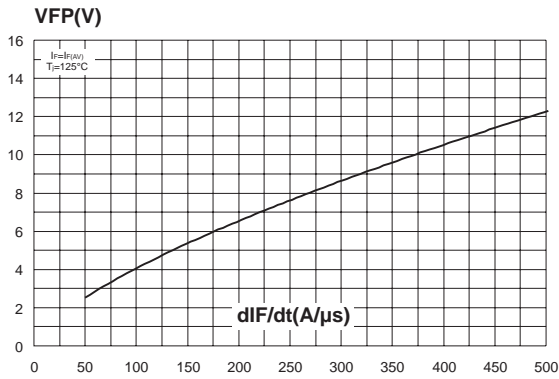


Fig. 10: Forward recovery time versus dI_F/dt (90% confidence).

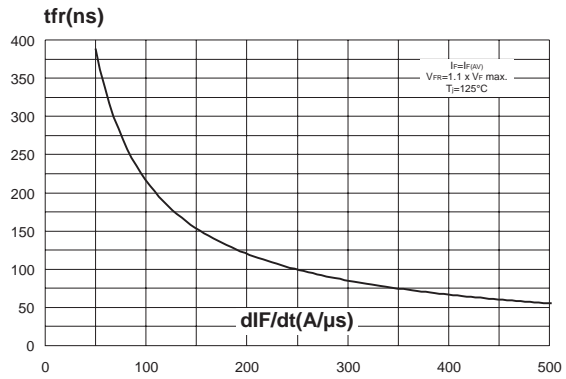
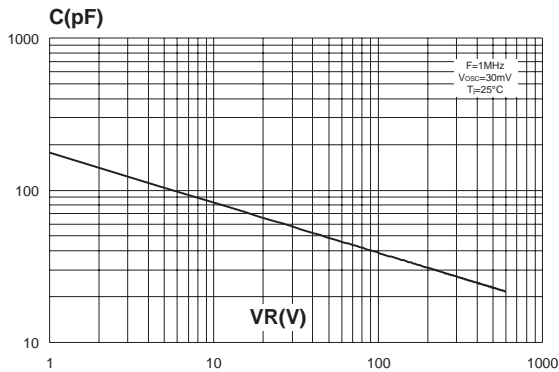
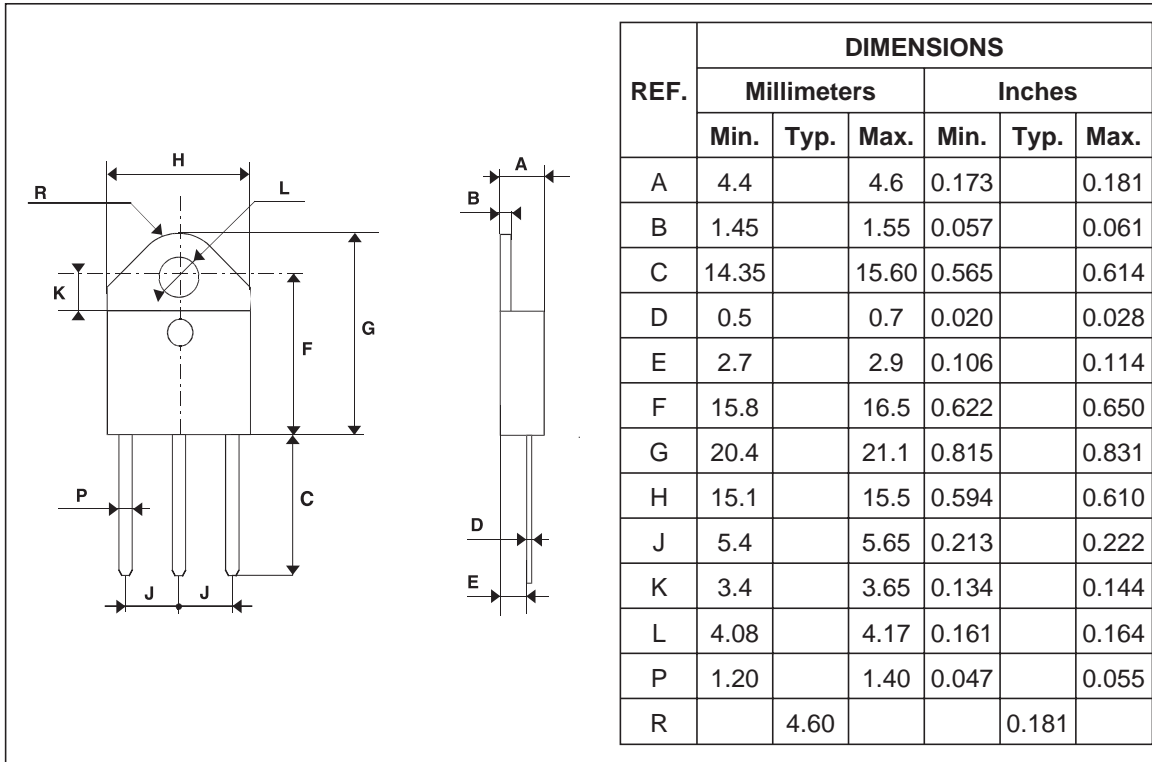


Fig. 11: Junction capacitance versus reverse voltage applied (typical values).



PACKAGE MECHANICAL DATA
TOP3I


Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH1506TPI	STTH1506TPI	TOP3I	4.46 g.	30	Tube

- Epoxy meets UL94,V0

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